

CAS-STN SEARCH
DONOT REMOVE!

**PROPERTY DATA AVAILABLE IN THE 'PROP' FORMAT*

2323 REFERENCES IN FILE CA (1957 TO DATE)

3 REFERENCES TO NON-SPECIFIC DERIVATIVES IN FILE CA

2325 REFERENCES IN FILE CAPLUS (1957 TO DATE)

51 REFERENCES IN FILE CAOLD (PRIOR TO 1967)

=> FIL CAPLUS HCAPLUS USPATFULL USPAT2

COST IN U.S. DOLLARS

SINCE FILE

TOTAL

ENTRY

SESSION

FULL ESTIMATED COST

29.36 29.57

FILE 'CAPLUS' ENTERED AT 13:33:37 ON 09 JUN 2003 USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT. PLEASE SEE "HELP USAGETERMS" FOR DETAILS. COPYRIGHT (C) 2003 AMERICAN CHEMICAL SOCIETY (ACS)

FILE 'HCAPLUS' ENTERED AT 13:33:37 ON 09 JUN 2003 USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT. PLEASE SEE "HELP USAGETERMS" FOR DETAILS. COPYRIGHT (C) 2003 AMERICAN CHEMICAL SOCIETY (ACS)

FILE 'USPATFULL' ENTERED AT 13:33:37 ON 09 JUN 2003
CA INDEXING COPYRIGHT (C) 2003 AMERICAN CHEMICAL SOCIETY (ACS)

FILE 'USPAT2' ENTERED AT 13:33:37 ON 09 JUN 2003
CA INDEXING COPYRIGHT (C) 2003 AMERICAN CHEMICAL SOCIETY (ACS)

=> d his

(FILE 'HOME' ENTERED AT 13:29:45 ON 09 JUN 2003)

FILE 'REGISTRY' ENTERED AT 13:29:51 ON 09 JUN 2003

L1 433 S SPARTEINE

L2 0 S SPARTEINE EX SAM

L3 3 S PENTROL

FILE 'CAPLUS, HCAPLUS, USPATFULL, USPAT2' ENTERED AT 13:33:37 ON 09 JUN 2003

=> s l1 or l3

L4 9341 L1 OR L3

=> s 14 and (resist or photoresist)

L5 18 L4 AND (RESIST OR PHOTORESIST)

=> duplicates remove 15

DUPLICATE PREFERENCE IS 'CAPLUS, HCAPLUS'

KEEP DUPLICATES FROM MORE THAN ONE FILE? Y/(N):n

PROCESSING COMPLETED FOR L5

L6 9 DUPLICATE REMOVE L5 (9 DUPLICATES REMOVED)

=> d l6 1-9 ibib

L6 ANSWER 1 OF 9 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 1

ACCESSION NUMBER:

2003:272171 CAPLUS

DOCUMENT NUMBER:

138:311557

TITLE:

Negative-working resist composition

containing alicyclic compound for x-ray and electron

INVENTOR(S):

Takahashi, Omote; Yasunami, Shoichiro; Adegawa, Yutaka

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 94 pp.

SOURCE:

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

APPLICATION NO. DATE

KIND DATE PATENT NO. ----

______ JP 2001-302633 20010928

JP 2003107705 A2 20030409 PRIORITY APPLN. INFO.:

JP 2001-302633 20010928

OTHER SOURCE(S):

MARPAT 138:311557

DUPLICATE 2

ANSWER 2 OF 9 CAPLUS COPYRIGHT 2003 ACS

DOCUMENT NUMBER:

ACCESSION NUMBER: 2000:356732 CAPLUS

TITLE:

133:11005

Radiation-sensitive resin composition

INVENTOR(S):

Chiba, Takashi; Kobayashi, Eiichi; Iwanaga,

Shinichirou

PATENT ASSIGNEE(S):

JSR Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 24 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

KIND DATE

APPLICATION NO. DATE

-----JP 1998-318802

19981110

JP 2000147773 A2 20000526 PRIORITY APPLN. INFO.:

PATENT NO.

JP 1998-318802

19981110

DUPLICATE 3

OTHER SOURCE(S):

MARPAT 133:11005

ANSWER 3 OF 9 CAPLUS COPYRIGHT 2003 ACS

DOCUMENT NUMBER:

ACCESSION NUMBER: 2000:143347 CAPLUS

TITLE:

132:201042

INVENTOR(S):

Radiation-sensitive resin composition useful as

resist Chiba, Takashi; Kobayashi, Eiichi; Iwanaga, Shinichiro

PATENT ASSIGNEE(S):

JSR Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 21 pp. CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

KIND DATE

APPLICATION NO. DATE -----

DUPLICATE 4

_____ JP 2000066382

JP 1998-236167

19980821

PRIORITY APPLN. INFO.:

PATENT NO.

A2 20000303

JP 1998-236167

19980821

ANSWER 4 OF 9 CAPLUS COPYRIGHT 2003 ACS

2000:441519 CAPLUS ACCESSION NUMBER:

DOCUMENT NUMBER:

133:81571

TITLE:

Photoresist composition suitable for deep-UV

wavelength imaging

INVENTOR(S):

Trefonas, Peter, III; Taylor, Gary N.

PATENT ASSIGNEE(S):

Shipley Company LLC, USA Eur. Pat. Appl., 14 pp.

CODEN: EPXXDW

DOCUMENT TYPE:

Patent English

LANGUAGE:

SOURCE:

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

KIND DATE PATENT NO. APPLICATION NO. DATE

_______ -----

EP 1014193 A1 20000628 EP 1999-125625 19991222

R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT,

IE, SI, LT, LV, FI, RO

JP 1999-376940 19991224 JP 2000298348 A2 20001024

PRIORITY APPLN. INFO.:

US 1998-219468 A 19981223

THERE ARE 6 CITED REFERENCES AVAILABLE FOR THIS REFERENCE COUNT: 6

RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

DUPLICATE 5

1.6 ANSWER 5 OF 9 CAPLUS COPYRIGHT 2003 ACS

1997:140435 CAPLUS

ACCESSION NUMBER: DOCUMENT NUMBER:

126:144674

TITLE:

Manufacture of carboxyl group- and ethylenic

unsaturated group-containing compounds and solder

resists containing them

INVENTOR(S):

Nakagawa, Sumie; Okazaki, Eiichi; Kato, Hitoshi

PATENT ASSIGNEE(S): Toa Gosei Kk, Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 12 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

_____ -----_____ JP 08301977 A2 19961119 JP 1995-129823 19950428

PRIORITY APPLN. INFO.:

JP 1995-129823 19950428

DUPLICATE 6

19850723

ANSWER 6 OF 9 CAPLUS COPYRIGHT 2003 ACS

1987:487210 CAPLUS

ACCESSION NUMBER:

DOCUMENT NUMBER: TITLE:

107:87210 Solid photosensitive polymer compositions

Yokoyama, Yasuaki; Fukuhara, Seiji; Nishiwaki, Koichi; INVENTOR(S):

Ikeda, Hiroharu

PATENT ASSIGNEE(S):

Japan Synthetic Rubber Co., Ltd., Japan

JP 1985-162580

SOURCE:

Jpn. Kokai Tokkyo Koho, 12 pp. CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PRIORITY APPLN. INFO.:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

______ -----JP 62023036 A2 19870131 JP 1985-162580 19850723

ANSWER 7 OF 9 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 7

ACCESSION NUMBER: 1987:487201 CAPLUS

DOCUMENT NUMBER: 107:87201

Liquid photosensitive polymer compositions TITLE:

Yokoyama, Yasuaki; Fukuhara, Seiji; Nishiwaki, Koichi; INVENTOR(S):

Ikeda, Hiroharu

PATENT ASSIGNEE(S):

Japan Synthetic Rubber Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 12 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

----------JP 1985-135135 19850620 JP 61292632 A2 19861223

PRIORITY APPLN. INFO.: JP 1985-135135 19850620

ANSWER 8 OF 9 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 8

ACCESSION NUMBER:

1985:176533 CAPLUS

DOCUMENT NUMBER:

SOURCE:

102:176533

TITLE:

Radiation-sensitive organic polymer resist

material

PATENT ASSIGNEE(S):

Hitachi, Ltd., Japan

Jpn. Kokai Tokkyo Koho, 5 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

---------______ A2 19841110 JP 59198448 JP 1983-72902 19830427

JP 03080301 B4 19911224

PRIORITY APPLN. INFO.: JP 1983-72902 19830427

ANSWER 9 OF 9 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 9

ACCESSION NUMBER: 1983:40606 CAPLUS

DOCUMENT NUMBER:

98:40606

TITLE:

Antidote for veterinary use to resist

poisoning with an organophosphate insecticide

INVENTOR(S): Popa, Ioan; Popescu, Maria; Bulete, Ionel

PATENT ASSIGNEE(S):

· Ministerul Apararii Nationale, Rom.

SOURCE:

Rom., 3 pp.

DOCUMENT TYPE:

CODEN: RUXXA3 Patent

LANGUAGE:

Romanian

FAMILY ACC. NUM. COUNT: 1

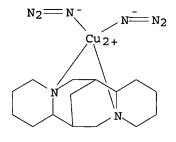
PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

----------RO 1973-76056 RO 66509 B 19781030 19730912

RO 1973-76056 PRIORITY APPLN. INFO.: 19730912

in the CAS Registry File, for complete details: http://www.cas.org/ONLINE/STN/STNOTES/stnotes27.pdf => s sparteine 433 SPARTEINE L1=> d ANSWER 1 OF 433 REGISTRY COPYRIGHT 2003 ACS L1 439901-24-3 REGISTRY RN Copper, diazido[(5S,7S,7aR,12S,14S,14aS)-dodecahydro-7,14-methano-2H,6H-CN dipyrido[1,2-a:1',2'-e][1,5]diazocine-.kappa.N5,.kappa.N12]-, (T-4)- (9CI) (CA INDEX NAME) OTHER NAMES: Bis(azido-.kappa.N) [(6R,7S,8S,14S)-(-)-sparteine-CN .kappa.2N,N']copper(II) MF C15 H26 Cu N8 CI CCS CA SR LC STN Files: CA, CAPLUS, CASREACT



2 REFERENCES IN FILE CA (1957 TO DATE)
2 REFERENCES IN FILE CAPLUS (1957 TO DATE)

=> s sparteine ex sam

SAMPLE IS IGNORED AS A SCOPE FOR THIS SEARCH

433 SPARTEINE

1747 EX

L2 0 SPARTEINE EX

(SPARTEINE (W) EX)

=> d l1 2

L1 ANSWER 2 OF 433 REGISTRY COPYRIGHT 2003 ACS

RN 340167-17-1 REGISTRY

CN Lithium, butyl[(5R,7S,7aR,12R,14S,14aR)-dodecahydro-7,14-methano-2H,6H-dipyrido[1,2-a:1',2'-e][1,5]diazocine-.kappa.N5,.kappa.N12]- (9CI) (CA INDEX NAME)

OTHER NAMES:

CN (-)-.alpha.-Isosparteine-butyllithium

FS STEREOSEARCH

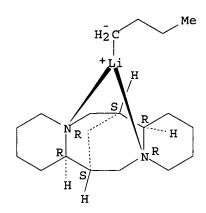
MF C19 H35 Li N2

CI CCS

SR CA

LC STN Files: CA, CAPLUS

Absolute stereochemistry.



1 REFERENCES IN FILE CA (1957 TO DATE)
1 REFERENCES IN FILE CAPLUS (1957 TO DATE)

=> d l1 4

L1 ANSWER 4 OF 433 REGISTRY COPYRIGHT 2003 ACS

RN 250138-49-9 REGISTRY

CN 7,14-Methano-2H,6H-dipyrido[1,2-a:1',2'-e][1,5]diazocine, dodecahydro-, monohydrobromide, (7S,7aS,14S,14aR)- (9CI) (CA INDEX NAME)

OTHER NAMES:

CN (-)-Sparteine monohydrobromide

FS STEREOSEARCH

MF C15 H26 N2 . Br H

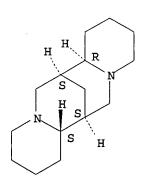
CI COM

SR CA

LC STN Files: CA, CAPLUS

CRN (90-39-1)

Absolute stereochemistry. Rotation (-).



• HBr

2 REFERENCES IN FILE CA (1957 TO DATE)

2 REFERENCES IN FILE CAPLUS (1957 TO DATE)

=> s pentrol

L3 3 PENTROL

```
L3
     ANSWER 1 OF 3 REGISTRY COPYRIGHT 2003 ACS
RN
     165724-61-8 REGISTRY
     Pentrol (pentaerythritol by-product) (9CI)
                                                      (CA INDEX NAME)
CN
OTHER NAMES:
CN
     Pentrol
ENTE A byproduct from synthesis of pentaerythritol (Russia)
ΜF
     Unspecified
CI
     MAN
SR
     CA
LC
     STN Files:
                   CA, CAPLUS, TOXCENTER
*** STRUCTURE DIAGRAM IS NOT AVAILABLE ***
                5 REFERENCES IN FILE CA (1957 TO DATE)
                5 REFERENCES IN FILE CAPLUS (1957 TO DATE)
     ANSWER 2 OF 3 REGISTRY COPYRIGHT 2003 ACS
L3
     17121-34-5 REGISTRY
RN
     2-Propanol, 1,1',1'',1'''-[[(2-hydroxypropyl)imino]bis(2,1-
CN
     ethanediylnitrilo)]tetrakis- (9CI) (CA INDEX NAME)
OTHER CA INDEX NAMES:
     2-Propanol, 1,1',1'',1'''-[[(2-hydroxypropyl)imino]bis(ethylenenitrilo)]te
CN
     tra- (8CI)
     2-Propanol, 1-[bis[2-[bis(2-hydroxypropyl)amino]ethyl]amino]- (7CI)
CN
OTHER NAMES:
     1,1',1'',1'''-[(2-Hydroxypropyl)iminobis(ethylenenitrilo)]tetra-2-propanol
CN
CN
     1,1,4,7,7-Pentakis(2-hydroxypropyl)-1,4,7-triazaheptane
     N, N, N', N', N''-Pentakis (2-hydroxypropyl) diethylenetriamine
CN
CN
     Pentrol
FS
     3D CONCORD
     C19 H43 N3 O5
MF
CI
     COM
                   BEILSTEIN*, CA, CAOLD, CAPLUS, CHEMCATS, CHEMLIST, CSCHEM,
LC
     STN Files:
       IFICDB, IFIPAT, IFIUDB, TOXCENTER, USPATFULL
          (*File contains numerically searchable property data)
                      EINECS**, NDSL**, TSCA**
     Other Sources:
          (**Enter CHEMLIST File for up-to-date regulatory information)
                                         OH
                  OH
                                    СH<sub>2</sub> — СН — Ме
    OH
             \mathtt{CH_2}-\mathtt{CH}-\mathtt{Me} \mathtt{CH_2}-\mathtt{CH_2}-\mathtt{N}-\mathtt{CH_2}-\mathtt{CH}-\mathtt{Me}
```

PROPERTY DATA AVAILABLE IN THE 'PROP' FORMAT

 $Me-CH-CH_2-N-CH_2-CH_2-N-CH_2-CH-Me$

24 REFERENCES IN FILE CA (1957 TO DATE)

OH

3 REFERENCES TO NON-SPECIFIC DERIVATIVES IN FILE CA

OH

- 24 REFERENCES IN FILE CAPLUS (1957 TO DATE)
- 1 REFERENCES IN FILE CAOLD (PRIOR TO 1967)
- L3 ANSWER 3 OF 3 REGISTRY COPYRIGHT 2003 ACS
- RN 54-95-5 REGISTRY
- CN 5H-Tetrazolo[1,5-a]azepine, 6,7,8,9-tetrahydro- (8CI, 9CI) (CA INDEX

```
NAME)
OTHER NAMES:
     .alpha.,.beta.-Cyclopentamethylenetetrazole
CN
     1,2,3,3a-Tetrazacyclohepta-8a,2-cyclopentadiene
     1,5-Pentamethylenetetrazole
CN
     6,7,8,9-Tetrahydro-5H-tetrazoloazepine
CN
CN
     7,8,9,10-Tetrazabicyclo[5.3.0]-8,10-decadiene
CN
     Angiazol
     Cardiazol
CN
CN
     Cardiazole
CN
     Cardiol
     Cenalene M
CN
CN
     Cenazol
     Cerebro-nicin
CN
CN
     Coranormal
CN
     Coranormol
CN
     Corasol
CN
     Corazol
CN
     Corazole
     Corazole (analeptic)
CN
CN
     Corisan
CN
     Corsedrol
CN
     Cortis
CN
     Corvasol
CN
     Delzol W
CN
     Deumacard
CN
     Gewazol
CN
     Korazol
CN
     Korazole
CN
     Leptazol
CN
     Leptazole
CN
     Metrazol
CN
     Metrazole
CN
     Pentamethylenetetrazole
CN
     Pentazol
CN
     Pentetrazol
CN
     Pentetrazole
CN
     Pentrazol
CN
     Pentrolone
CN
     Pentrozol
CN
     Pentylenetetrazol
CN
     Pentylenetetrazole
CN
     Phrenazol
CN
     PTZ
CN
     Tetracor
CN
     Tetrazol
     Tetrazole, (1,5-pentanediyl)-
CN
CN
     Ventrazol
CN
     Yetrazol
FS
     3D CONCORD
MF
     C6 H10 N4
CI
     COM
LC
                   ADISNEWS, AGRICOLA, ANABSTR, BEILSTEIN*, BIOBUSINESS, BIOSIS,
     STN Files:
       BIOTECHNO, CA, CANCERLIT, CAOLD, CAPLUS, CASREACT, CEN, CHEMCATS,
       CHEMINFORMRX, CHEMLIST, CIN, CSCHEM, DDFU, DETHERM*, DIOGENES, DRUGU,
       EMBASE, GMELIN*, HODOC*, IFICDB, IFIPAT, IFIUDB, IPA, MEDLINE, MRCK*, MSDS-OHS, NIOSHTIC, PHARMASEARCH, PROMT, RTECS*, SPECINFO, TOXCENTER,
       USAN, USPAT2, USPATFULL, VETU
          (*File contains numerically searchable property data)
     Other Sources: EINECS**, NDSL**, TSCA**, WHO
          (**Enter CHEMLIST File for up-to-date regulatory information)
```

=> d 117 1-48 ibib abs

L17 ANSWER 1 OF 48 CAPLUS COPYRIGHT 2003 ACS

2003:200566 CAPLUS

ACCESSION NUMBER: DOCUMENT NUMBER:

138:245598

TITLE:

Negative-working chemically amplified electron beam or

DUPLICATE 1

x-ray resist composition with controlled

water content

INVENTOR (S):

Adegawa, Yutaka

PATENT ASSIGNEE(S): SOURCE:

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 82 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE ----------A2 20030314 JP 2001-271992 JP 2003076020 20010907 JP 2001-271992 PRIORITY APPLN. INFO.: 20010907

The title compn. contains an electron beam- or x-ray-sensitive

acid generator, an alkali solubilizable resin,

an acid-sensitive crosslinking agent, and an org. basic compd., wherein the water content in the compn. is .ltoreq.0.5%. The compn. provides the resist of high resoln. and high evenness on the line width and is suitable for use for semiconductor device fabrication.

L17 ANSWER 2 OF 48 USPATFULL

ACCESSION NUMBER:

2003:51058 USPATFULL

TITLE:

Resist with reduced line edge roughness

INVENTOR(S):

Fedynyshyn, Theodore H., Sudbury, MA, UNITED STATES

KIND NUMBER DATE ------

PATENT INFORMATION:

US 2003036015 A1 20030220

APPLICATION INFO.:

(9) 5/9/01 A1 US 2001-851952 20010509

DOCUMENT TYPE: FILE SEGMENT:

Utility APPLICATION

LEGAL REPRESENTATIVE:

NUTTER MCCLENNEN & FISH LLP, WORLD TRADE CENTER WEST,

155 SEAPORT BOULEVARD, BOSTON, MA, 02210-2604

NUMBER OF CLAIMS:

49

EXEMPLARY CLAIM:

LINE COUNT:

1225

linewidth resolution.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

Novel photoresists containing at least about 0.2 molar ratio of a base with respect to the concentration of a photoacid generator present and their preparation are described. It has been discovered that inclusion of a sufficient amount of base counteracts the detrimental effects of photoacid generators, thus providing resists having submicron

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L17 ANSWER 3 OF 48 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 2

ACCESSION NUMBER:

2002:869230 CAPLUS

DOCUMENT NUMBER:

137:377442

TITLE:

Photoresist with reduced line edge roughness

INVENTOR(S):

Fedynydhyn, Theodore H.

PATENT ASSIGNEE(S):

Massachusetts Institute of Technology, USA

SOURCE:

PCT Int. Appl., 35 pp.

CODEN: PIXXD2

DOCUMENT TYPE:

Patent English

LANGUAGE: PATENT INFORMATION:

FAMILY ACC. NUM. COUNT:

KIND DATE APPLICATION NO. DATE PATENT NO.

WO 2002091084 A2 20021114 WO 2002-US14671 20020509

W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH,

GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH,

PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TN, TR, TT, TZ,

UA, UG, UZ, VN, YU, ZA, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, RW: GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW, AT, BE, CH,

CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG

US 2001-851952 20010509 US 2003036015 A1 20030220

PRIORITY APPLN. INFO.:

US 2001-851952 A 20010509

Novel photoresists contg. at least about 0.2 molar ratio of a

base with respect to the concn. of a photoacid generator are disclosed and their prepn. are described. It has been discovered that inclusion of a sufficient amt. of base counteracts the detrimental effects of photoacid generators, thus providing resists having submicron linewidth resoln.

L17 ANSWER 4 OF 48 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 3

ACCESSION NUMBER:

2002:978378 CAPLUS

DOCUMENT NUMBER:

138:63823

TITLE:

Photoresist compositions comprising silyl

ketals and methods of use thereof Huang, Wu-song; Medeiros, David R.

INVENTOR(S): PATENT ASSIGNEE(S):

International Business Machines Corporation, USA

SOURCE:

U.S. Pat. Appl. Publ., 10 pp. CODEN: USXXCO

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

KIND DATE APPLICATION NO. DATE PATENT NO.

______ ______ US 2001-882234 US 2002197556 A1 20021226 20010615

PRIORITY APPLN. INFO.:

US 2001-882234 20010615

A chem. amplified resist compn. comprises an aq. base sol.

polymer or copolymer having one or more polar functional groups, wherein at least one of the functional groups is protected with a silyl ketal group but may also include other protecting groups as well as unprotected acidic functionalities. A ratio of protected to unprotected acidic functionalities is preferably selected to most effectively modulate a soly. of the resist compn. in an aq. base or other developer.

The resist compn. further comprises an acid

generator, preferably a photoacid generator

(PAG), and a casting solvent, and may also include other components, such as, a base additive and/or surfactant.

L17 ANSWER 5 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 4

2002:327849 CAPLUS ACCESSION NUMBER:

DOCUMENT NUMBER: 136:348308

TITLE: Polymers and positive-acting photoresist

compositions comprising same

Trefonas, Peter, III; Taylor, Gary N.; Barclay, George INVENTOR(S):

. PATENT ASSIGNEE(S):

Shipley Company, L.L.C., USA

SOURCE:

U.S., 11 pp. CODEN: USXXAM

DOCUMENT TYPE:

Patent

English

LANGUAGE:

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE ----------US 2000-510069 20000222 US 6379861 B1 20020430 PRIORITY APPLN. INFO.: US 2000-510069 20000222 The present invention provides novel polymers and photoresist

compns. that comprise the polymers as a resin binder component in chem.-amplified, pos.-acting resists. The photoresist compns. of the invention can provide highly resolved relief images upon exposure to short wavelengths, including 193 nm and 248 nm. The resists of the invention are also useful or imaging at other wavelengths such as 365 nm. Polymers of the invention include those that comprise a photogenerated acid-labile unit that is ester group that comprises an alkyl moiety having .apprx.5 or more C atoms and .gtoreq.2 secondary, tertiary or quaternary C atoms. The alkyl moiety of the ester group can be a noncyclic or single ring alicyclic group. The carboxyl (C=O(O)) O of the ester group is often preferably directly bonded to a quaternary C atom.

REFERENCE COUNT:

THERE ARE 12 CITED REFERENCES AVAILABLE FOR THIS 12 RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L17 ANSWER 6 OF 48 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 5

ACCESSION NUMBER:

2002:848227 CAPLUS

DOCUMENT NUMBER:

137:360309

TITLE:

Radiation-sensitive positive resist

compositions showing wide defocus latitude and less

particle generation on storage Kodama, Kunihiko; Sato, Kenichiro

PATENT ASSIGNEE(S): SOURCE:

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 90 pp.

INVENTOR(S):

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE		APPLICATION N	10.	DATE		
	- -							
JP 2002323767	A2	20021108		JP 2001-157366		20010525		
US 2003017415	A1	20030123		US 2002-79414	Į.	20020222		
PRIORITY APPLN. INFO	. :		JP	2001-48602	Α	20010223		
			JP	2001-48783	Α	20010223		
			JP	2001-48784	Α	20010223		
			JP	2001-48880	Α	20010223		
			JP	2001-157366	Α	20010525		
			JP	2001-157367	Α	20010525		

AB The compns., esp. suited for deep-UV lithog., comprise acid generators contg. triarylsulfonium salts and phenathylsulfonium salts, alicyclic hydrocarbon resins increasing alkali soly. upon reaction with acids, bases, and fluoro and/or silicone surfactants,. The compns. may contain OH-bearing and -free solvent mixts.

L17 ANSWER 7 OF 48 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 6

ACCESSION NUMBER:

2002:734115 CAPLUS 137:270526

DOCUMENT NUMBER: TITLE:

Positive-working photoresists with high

sensitivity and good resolution on development

INVENTOR(S): PATENT ASSIGNEE(S): Fujimori, Toru; Takita, Satoshi; Itabashi, Hideyuki Fuji Photo Film Co., Ltd., Japan; Fujifilm Arch K. K.

Jpn. Kokai Tokkyo Koho, 44 pp.

SOURCE:

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE ----______ ______ A2 20020927 JP 2001-81164 20010321 JP 2002278071 PRIORITY APPLN. INFO.: JP 2001-81164 20010321

OTHER SOURCE(S):

MARPAT 137:270526

The compns. contain (A) radiation-induced acid-generating compds., (B) resins having mono- or polyalicyclic hydrocarbyl structure and being decomposable by acid to become dissolvable in alkali developing soln., and (C) an arom. carboxylic acid with protective group. Thus, adding over 4 h a soln. of 2-methyl-2-adamantyl methacrylate 5.0, mevalonic lactone methacrylate 4.23, V-65 (azo radical initiator) 0.534 and AcNMe2 30.0 to AcNMe2 7.0 g heated at 60.degree., reacting for 2 h, further adding 0.267 V-650, reacting for 2 h and working up gave a copolymer with Mw 5500 and Mw/Mn 1.9. Mixing 9.0 parts the copolymer with triphenylsulfonium triflate 0.1, tetrahydro-2-pyranyl benzoate 1.0, 1,5-diazabicyclo[4.3.0]-5-nonene 0.005 and Megafac F 176 (surfactant) 0.01 parts, dilg. in propylene glycol monomethyl ether acetate to a solids content of 15%, filtering, spin coating on a silane-primed Si wafer, and drying at 120.degree. for 90 s gave a photoresist layer which was then patterned using a photomask and ArF excimer laser stepper and developed with tetramethylammonium hydroxide to give patterns with good resoln.

L17 ANSWER 8 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 7

ACCESSION NUMBER:

2002:734102 CAPLUS

DOCUMENT NUMBER:

137:270516

TITLE:

Positive-working electron-beam or x-ray resist

composition

INVENTOR(S):

Adegawa, Yutaka; Nakamura, Ippei Fuji Photo Film Co., Ltd., Japan

PATENT ASSIGNEE(S): SOURCE:

Jpn. Kokai Tokkyo Koho, 72 pp. CODEN: JKXXAF

DOCUMENT TYPE:

Patent Japanese

LANGUAGE:

FAMILY ACC. NUM. COUNT: PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
	-			
JP 2002278052	A2	20020927	JP 2001-76688	20010316
US 2003039916	A1	20030227	US 2002-62497	20020205
PRIORITY APPLN. INFO.	:		JP 2001-28336 A	20010205
			JP 2001-76688 A	20010316

MARPAT 137:270516 OTHER SOURCE(S): The resist compn. contains a photoacid

 $\mbox{\tt generator}$ generating an acid upon irradn. with electron beam or xray, a cyclic ether, and an org. basic compd. The compn. shows high sensitivity and high PBD (post bake delay) stability and provides sharp-edge pattern profile.

L17 ANSWER 9 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 8

ACCESSION NUMBER: 2002:553401 CAPLUS

DOCUMENT NUMBER: 137:132096

Positive-working photoresist composition TITLE: containing alkylene glycol alkyl ether

INVENTOR(S):

Fujimori, Toru; Nakao, Hajime Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 43 pp.

CODEN: JKXXAF

DOCUMENT TYPE: LANGUAGE:

SOURCE:

Patent Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT ASSIGNEE(S):

PATENT NO. KIND DATE APPLICATION NO. DATE

------ ---- ----------JP 2001-2860 20010110 JP 2001-2860 20010110 JP 2002207289 A2 20020726 PRIORITY APPLN. INFO.:

OTHER SOURCE(S): MARPAT 137:132096

The compn. contains (A) a compd. generating an acid by actinic ray or radiation, (B) a resin with mono- or poly-cyclic aliph. hydrocarbon structure and its soly. to alk. developer increases by the action of an acid, and (C) R1(OX)mOR2 (R1-2 = linear, branched, or cyclic alkyl; X = linear, branched, or cyclic alkylene; m, l = 1-9). The compn. contains (A), (C), (D) dissoln. inhibitor with mol. wt. .ltoreq.3000 having acid-decomposable group and whose soly. to an alk. developer increases by the action of an acid., and (E) a resin insol. in water and sol. in an alk. developer. The compn. shows high sensitivity, resoln. and generation of const. wave on resist surface is prevented.

L17 ANSWER 10 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 9

ACCESSION NUMBER: 2002:364226 CAPLUS DOCUMENT NUMBER: 136:393267

TITLE:

Positive-working resist compositions with

high sensitivity and resolution

INVENTOR(S):

Fujimori, Toru; Tan, Shiro; Nakao, Hajime

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

Jpn. Kokai Tokkyo Koho, 43 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

SOURCE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

KIND DATE PATENT NO. APPLICATION NO. DATE ______ -----JP 2002139839 A2 20020517 JP 2000-332955 20001031 PRIORITY APPLN. INFO.: JP 2000-332955 20001031

MARPAT 136:393267 OTHER SOURCE(S):

The compns. contain photoacid generators (A), polymers (B) having alicyclic hydrocarbon structures in the main or side chains and good soly. in alkali developing agents by acid-induced decompn., and compds. (C) shown as RXC:OOH (R = F-contg. hydrocarbyl; X = F-free divalent linking group). The compns., useful for microphotofabrication using ArF excimer laser in semiconductor device fabrication, give resist patterns with good pattern profiles and reduced standing wave effect.

L17 ANSWER 11 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 10

ACCESSION NUMBER: 2002:364224 CAPLUS

DOCUMENT NUMBER: 136:393265

TITLE: Chemically-amplified negative-working resist

compositions containing radical generators

INVENTOR(S): Adegawa, Yutaka

Fuji Photo Film Co., Ltd., Japan PATENT ASSIGNEE(S): SOURCE: Jpn. Kokai Tokkyo Koho, 83 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2002139836 A2 20020517 JP 2000-336334 20001102

PRIORITY APPLN. INFO.: JP 2000-336334 20001102

AB The compns., which show high sensitivity, high resoln., rectangular pattern profile, and PCD (post coating delay) and PED (post exposure delay) stability, contain (a) compds. which directly or indirectly generate radicals upon irradn. with energy ray. The compns. may contain (b) compds. which generate acids upon irradn. with energy ray, (c) alkali-sol. resins, and (d) crosslinking agents reacting by acids.

L17 ANSWER 12 OF 48 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 11

ACCESSION NUMBER: DOCUMENT NUMBER:

2002:347848 CAPLUS

136:361828

TITLE:

Positive-working **photoresist** compositions

containing norbornene-acrylate copolymers

INVENTOR(S):

Sato, Kenichiro; Nakao, Hajime

PATENT ASSIGNEE(S): SOURCE:

Fuji Photo Film Co., Ltd., Japan

Jpn. Kokai Tokkyo Koho, 80 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE		APPLICATION 1	. OI	DATE
JP 2002131917	A2	20020509		JP 2001-16980	02	20010605
PRIORITY APPLN. INFO.	:		JP	2000-174037	Α	20000609
			JP	2000-186431	Α	20000621
			JP	2000-206812	Α	20000707
			JP	2000-206890	Α	20000707
			JP	2000-211414	Α	20000712
			JP	2000-215441	Α	20000717
			JP	2000-248658	Α	20000818

MARPAT 136:361828

OTHER SOURCE(S):

GI

AB The compns., which show wide defocus latitude, reduced line edge roughness, and high resoln., contain (A) resin which increases its soly. in alk. developers upon reaction of acids and contain (a) a repeating unit I [R11-R14 = H, (un)substituted alkyl; a = 0, 1] and (b) CH2CR1(ACO2W) (R1 = H, Me; A = direct bond, alkylene, cycloalkylene, O, ether group, thioether group, O, ester group; W = Q, CR16R17R18,

CHR20OR19, CR23R25CR21:CR22R24, R26R29CHR27COR28, Q1; R15 = Me, Et, Pr, CHMe2, Bu, CH2CMe2, CHMeEt; Z = at. group required to form an alicyclic ring; R16-R20 = C1-4 linear or branched alkyl, alicyclyl; .gtoreq.1 of R16-R18, R19 or R20 = alicyclyl; R21-R25 = H, C1-4 linear or branched alkyl, alicyclyl; .gtoreq.1 R21-R25 = alicyclyl; R23 or R25 = C1-4 linear or branched alkyl, alicyclyl; R26-R29 = C1-4 linear or branched alkyl, alicyclyl; .gtoreq.1 of R26-R29 = alicyclyl), (B) compds. which generate acids upon irradn. of actinic ray or radiation, and optionally (C1) R[X(CR51CR52)qCO2R1]n (X = 0, S, NR53, direct bond, R53 = H, alkyl; CO2R1 = acid-decomposable group; R = n-valent bridged hydrocarbon ring, satd. cyclic hydrocarbon ring, naphthalene ring; n = 1-4; q = 0-10), (C2) naphthalene derivs. II (R60 = alkyl, halo; OR61 = acid-decomposable group; m = 0-4; p = 1-4), or (C3) steroid compds. which contain .gtoreq.2 substituents having .gtoreq.1 carboxyl group protected with acid-labile group. The acid generators may be imide sulfonate compds. or diazodisulfonic acids (Markush structures are given) and optionally sulfonium salts. (C1)-(C3) work as dissoln. inhibitors and the compns. give high-resoln. contact hole and trench patterns in fabrication of semiconductor devices.

L17 ANSWER 13 OF 48 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 12

ACCESSION NUMBER:

2002:347846 CAPLUS

DOCUMENT NUMBER:

SOURCE:

136:361827

TITLE:

Positive-working photoresist composition

suitable for ArF excimer laser exposure

INVENTOR(S):

Kawabe, Yasumasa

CODEN: JKXXAF

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan

Jpn. Kokai Tokkyo Koho, 24 pp.

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2002131914 A2 20020509 JP 2000-327358 20001026
PRIORITY APPLN. INFO.: JP 2000-327358 20001026

OTHER SOURCE(S):

MARPAT 136:361827

GI

A pos.-working chem. amplification photoresist compn. comprises (A) a cycloaliph. polymer capable of becoming alk.-sol. upon acid-induced decompn., (B) a photoacid generator(s) capable of releasing acid upon .ltoreq.220 nm light irradn., (C) a compd. represented by I (R1-2, R5-8, R11-12 = H, OH, halo, C1-4-alkyl, C1-4-alkoxy; R3-4, R9-10 = C1-4-alkyl; X = H; X joining together with R1 may form ring; Y = H, Ph, substituted phenyl) or II (R18-27 = H, OH, halo, C1-4-alkyl, C1-4-alkoxy; R22 joining together with R23 may form ring), and (D) a fluoro- and/or silicone-surfactant(s), and optionally (E) an acid trapping agent. The photoresist compn. may contain a low mol. wt. compd. having an acid decomposable group and a group capable of becoming alk .- sol. upon contact with an acid. The photoresist compn. shows improved line edge roughness and is suitable for semiconductor device fabrications by ArF excimer lasers.

L17 ANSWER 14 OF 48 CAPLUS COPYRIGHT 2003 ACS ACCESSION NUMBER:

2002:345226 CAPLUS

DOCUMENT NUMBER:

136:361820

TITLE:

Chemically amplified positive photosensitive polymer

DUPLICATE 13

compositions for resists with high

resolution

INVENTOR (S):

Kawabe, Yasumasa

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 22 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

SOURCE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE -----JP 2002131913 A2 20020509 JP 2000-327357 20001026 JP 2000-327357 PRIORITY APPLN. INFO.: 20001026

OTHER SOURCE(S):

MARPAT 136:361820

The compns., useful for semiconductor device fabrication, printed circuit board manuf., etc., comprise (A) polymers having alicyclic hydrocarbon blocks, which become alkali-sol. by acid decompn., (B) radiation-sensitive acid generators, (C) XCR10HCR20HY or X(C:NOH)2Y (R1, R2
= H, C1-4-alkyl, Ph; R3, R4 = halo, C1-4-alkyl, trifluoromethyl; X = C6H5-lR3l; Y = C6H5-mR4m; l, m = 0-3), and (D) fluoro and/or silicone surfactants. The resist compns. are sensitive to ArF excimer laser beams.

L17 ANSWER 15 OF 48 CAPLUS COPYRIGHT 2003 ACS **DUPLICATE 14**

ACCESSION NUMBER:

2002:349275 CAPLUS

DOCUMENT NUMBER:

136:377476

TITLE:

Chemically amplified positive-working

photoresist compositions for excimer laser

development with high sensitivity and resolution

Fujimori, Toru; Tan, Shiro; Nakao, Hajime

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 44 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

INVENTOR(S):

Patent

LANGUAGE:

SOURCE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE ____ -----JP 2002131910 A2 20020509 JP 2000-325915 20001025 PRIORITY APPLN. INFO.: JP 2000-325915 20001025 AB The compns. comprise (A) photoacid generators, (B)
resins having alicyclic hydrocarbon structures, which are decompd.
by acids to increase their alkali-soly., and (C) RWCO2B (R = alkyl,
alicyclic ring-contg. group; W = divalent org. group; B =
acid-decomposable group). The photoresists are useful for
micro-photofabrication by far UV radiation at .ltoreg.250 nm wavelength.

L17 ANSWER 16 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 15

ACCESSION NUMBER: 2002:176284 CAPLUS

DOCUMENT NUMBER: 136:239101

TITLE: Positive-working photoresist compositions

containing carboxy-terminated fluorine-containing

polyethers

INVENTOR(S): Kawabe, Yasumasa; Kanna, Shinichi PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 38 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

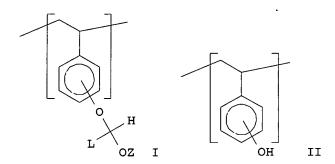
Patent Japanese

LANGUAGE: J FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2002072482 A2 20020312 JP 2000-265558 20000901
PRIORITY APPLN. INFO: JP 2000-265558 20000901
GI



AB The compn. contains (A) photoacid generators, (B) polymers insol. or hardly sol. in alkali but become alkali-sol. by treatment with acids, and (C) carboxylic acid derivs. having mol. wt. .ltoreq.1000 and having partial structure (CR22)nO(CR12)mCO2H (R1 = H, F, CF3; R2 = H, F, CF3, OR3; R3 = C1-4 alkyl, fluoroalkyl; m, n = integer of 1-3; R1 and/or R2 contain F). Preferably, component B contains structural repeating units I and II (L = H, (un)substituted linear, branched, or cyclic alkyl, (un)substituted aralkyl; Z = (un)substituted linear, branched, or cyclic alkyl, (un)substituted aralkyl; Z + L may form 5- or 6-membered ring). The compns. may also contain N-contg. basic compds. and fluoro- and/or Si-contg. surfactants. Formation of defects on development is prevented. The compns. are suitable in fabrication of semiconductor devices.

L17 ANSWER 17 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 16

ACCESSION NUMBER: 2002:176283 CAPLUS

DOCUMENT NUMBER: 136:239100

TITLE: Positively working photoresist composition

for suppression of development defect

INVENTOR(S): Kawabe, Yasumasa

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 18 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2002072481 A2 20020312 JP 2000-265557 20000901

PRIORITY APPLN. INFO.:

AB The compn. comprises (A) polymer with alicyclic hydrocarbon structure which becomes alkali sol. by acid decompn., (B) acid generator sensitive to actinic ray or radiation, (C) C4-20 aliph. (di)carboxylic acid including .gtoreq.4 F atoms per mol. and having mol. wt. .ltoreq.1000, (D) N-contg. basic compd., and (E) F- and/or Si-contg. surfactant. The compn. has high sensitivity, and defect-free resist patterns with high size accuracy, resoln., and low line edge roughness can be formed.

L17 ANSWER 18 OF 48 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 17

ACCESSION NUMBER:

2002:119603 CAPLUS

DOCUMENT NUMBER: TITLE:

136:191685

Positively working photoresist composition

for far-ultraviolet exposure

INVENTOR(S):
PATENT ASSIGNEE(S):

Nakao, Hajime; Sato, Kenichiro Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 55 pp.

SOURCE:

Jpn. Kokai Tokkyo Koho, 55 pp. CODEN: JKXXAF

DOCUMENT TYPE: P

LANGUAGE:

Patent Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2002049154 A2 20020215 JP 2000-233146 20000801
PRIORITY APPLN. INFO.: JP 2000-233146 20000801

OTHER SOURCE(S):

MARPAT 136:191685

GΙ

AΒ

Me Me
$$(R60)_{m1}$$
 $(OR61)_{p1}$ II $R12$ $R14$ $R14$

The compn., useful for ultramicrolithog. process in fabrication of ultra-large-scale integrated circuits (ULSI), contains (A) polymers having

alicyclic repeating unit I [R11-R14 = H, (substituted) alkyl; a = 0, 1] and [CH2CR(ACO2W)] unit [R1 = H, Me; A = none, alkylene, cycloalkylene, O, S, CO, and/or ester; W = CRaRbRc, CHRdORe; Ra-Rc, Re = (halo-, alkoxy-, alkoxycarbonyl, acyl-, or acyloxy-substituted) C1-20 linear or branched alkyl, C3-20 cycloalkyl; Ra and Rb may form an alicyclic ring; Rd = H, alkyl] to increase alkali developability by acids, (B) photoacid generators, and (C) R[X(CR51R52)qCO2R']n (II; X = O, S, NR53, none; R51-R53 = H, alkyl; R' = acid-degradable group as CO2R'; R = bridged hydrocarbon, satd. alicyclic compd., naphthalene-contq. n-valent residue; n = 1-4; q = 0-10), naphthalene derivs. III (R60 = alkyl, halo; R61 = acid-degradable group as OR61; m = 0-4; p = 1-4), or a cholic acid deriv. having structure IV substituted with .gtoreq.2 groups having .gtoreq.1 substituent contq. carboxyl group protected with acid-unstable group. The compds. II-IV work as dissoln. inhibitors and the compn. gives high-resoln. contact hole and trench patterns in fabrication of semiconductor devices.

L17 ANSWER 19 OF 48 USPATFULL

ACCESSION NUMBER: 2002:16787 USPATFULL

TITLE: Positive **photoresist** composition INVENTOR(S): Sato, Kenichiro, Shizuoka, JAPAN Aoai, Toshiaki, Shizuoka, JAPAN

PRIORITY INFORMATION: JP 2000-115497 20000417
JP 2000-215574 20000717
JP 2000-231670 20000731

DOCUMENT TYPE: Utility
FILE SEGMENT: APPLICATION

LEGAL REPRESENTATIVE: SUGHRUE, MION, ZINN, MACPEAK & SEAS, PLLC, 2100

Pennsylvania Avenue, N.W., Washington, DC, 20037

NUMBER OF CLAIMS: 18
EXEMPLARY CLAIM: 1
LINE COUNT: 1642

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AB Provided is a positive **photoresist** composition comprising a **resin** which contains specific repeating units and whose dissolving rate toward an alkaline developing solution is increased by the action of an acid and a compound which generates an acid upon irradiation with an actinic ray or a radiation.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L17 ANSWER 20 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 18

ACCESSION NUMBER: 2002:669862 CAPLUS

DOCUMENT NUMBER: 137:343818

TITLE: The Multifunctional Role of Base Quenchers in

Chemically Amplified Photoresists

AUTHOR(S): Pawloski, Adam R.; Christian; Nealey, Paul F.

CORPORATE SOURCE: Center for Nanotechnology and Department of Chemical

Engineering, University of Wisconsin, Madison, WI,

53706, USA

SOURCE: Chemistry of Materials (2002), 14(10), 4192-4201

CODEN: CMATEX; ISSN: 0897-4756

PUBLISHER: American Chemical Society

DOCUMENT TYPE: Journal LANGUAGE: English

AB A systematic investigation of four base quenchers in chem. amplified

photoresist revealed that the role of the base quencher is more complex than rapid, stoichiometric neutralization of photoacid. quenchers studied included common supplements to chem. amplified photoresist, 1,8-diazabicyclo[5.4.0]undec-7-ene (DBU), 1-piperidineethanol (1PE), and tetrabutylammonium hydroxide (TBAH), and an atm. contaminant and poison to chem. amplified resists, N-Me pyrrolidinone (NMP). Acid-base neutralization, deprotection, and development processes in formulations with and without base quencher were evaluated to det. the effects of the base quencher on resist processing. The extent of deprotection of the polymer was measured by IR spectroscopy and analyzed as a function of the concn. of photoacid within the resist. The concn. of photoacid after exposure was detd. using a std. addn. technique that quantified the efficiency of photoacid generation. Dissoln. rates were measured as a function of the extent of deprotection, and the induction time during development was measured as a function of the resist dissoln. rate. Some base quenchers were found (i) to neutralize photoacid in the resist with less than stoichiometric proportions, (ii) to act as dissoln. inhibitors or promoters, and (iii) to lengthen the induction time during development. These results show that base quenchers act in considerably more complex ways than the stoichiometric neutralization of photogenerated acid, and understanding these multifunctional characteristics is important for the design of improved resist systems for high-resoln. lithog.

REFERENCE COUNT: 16 THERE ARE 16 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L17 ANSWER 21 OF 48 CAPLUS COPYRIGHT 2003 ACS

JS COPYRIGHT 2003 ACS DUPLICATE 19

ACCESSION NUMBER:

2001:726601 CAPLUS

DOCUMENT NUMBER:

135:280511

TITLE:

SOURCE:

Positive-working **photoresist** compositions

showing high resolution and high sensitivity and

excellent storage stability

INVENTOR(S):

Sato, Kenichiro

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 62 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

PE: Patent

LANGUAGE: Japanese FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2001272784 A2 20011005 JP 2000-385724 20001219

PRIORITY APPLN. INFO.: JP 1999-363302 A 19991221

JP 2000-10773 A 20000119

JP 2000-10774 A 20000119

OTHER SOURCE(S): MARPAT 135:280511

The compns. contain (A) compds. generating acid on irradn. of actinic ray or radiation, (B) polymers contg. structural repeating unit CO2CR1R2(CR3R4)mSiR5R6R7 (R1-2 = (cyclic) alkyl; R3-4 = H, (cyclic) alkyl; R1 + R2, R3 + R4 may form cyclic alkyl; R5-7 = (cyclic) alkyl, aryl, trialkylsilyl(oxy); m = integer of 1-6) and increasing soly. in alk. developing agents by reaction with acids, (C) org. basic compds., and (D) .gtoreq.1 of F-contg. surfactants, Si-contg. surfactants, and nonionic surfactants. Preferable structural repeating units also contained in the polymers are given in Markush. Also claimed are (1) compns. consisting of (A') acid-generating sulfonium salts Rs1S+ Rs2Rs3 Z- (Rs1-3 = (un)substituted alkyl or aryl; Rs1 + Rs2 may bond via single bond or bonding group; Z- = anion) and polymers B and (2) compns. consisting of acid generators A, polymers B, and certain surfactants given in the document. The compns. are useful in manuf. of semiconductor devices, printed circuits, liq. crystal panels, etc.

L17 ANSWER 22 OF 48 CAPLUS COPYRIGHT 2003 ACS

2001:595544 CAPLUS

ACCESSION NUMBER: DOCUMENT NUMBER:

135:187705

TITLE:

Positive-working photoresist composition for

excimer layer

INVENTOR(S): PATENT ASSIGNEE(S): Kawabe, Yasumasa; Yamanaka, Tsukasa Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 38 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

SOURCE:

FAMILY ACC. NUM. COUNT:

Japanese

PATENT INFORMATION:

PATENT NO. KIND DATE ---- -----------

APPLICATION NO. DATE

DUPLICATE 20

JP 2001222110 A2 20010817

JP 2000-33621

20000210

PRIORITY APPLN. INFO.:

JP 2000-33621

The pos. photoresist compn. contains (A) a compd. generating acid by the irradn. of actinic ray or radiation, (B) a resin which is insol. or slightly sol. in alkali and becomes sol. in alkali by

the action of an acid, (C) a carboxylic anhydride with mol. wt. .ltoreq.1000, (D) N-contg. basic compd., and (E) a fluorosurfactant and/or a silicone surfactant. The resist compn. is useful for KrF

excimer laser irradn., gives clear patterns without defect, and useful for semiconductor device manuf.

L17 ANSWER 23 OF 48 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 21

ACCESSION NUMBER: DOCUMENT NUMBER:

2001:541847 CAPLUS 135:129575

TITLE:

Positive photoresist compositions containing

norbornene polymers bearing silicon-containing

branches

INVENTOR(S):

Mizutani, Kazuyoshi

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 42 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

SOURCE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

KIND DATE

APPLICATION NO. DATE -----

PATENT NO. JP 2001201860

---- -----A2 20010727

JP 2000-8042

20000117

PRIORITY APPLN. INFO.:

JP 2000-8042

20000117

GΙ

MSiR1R2R3

AB The pos. photoresist compns. contain polymers contg. repeating units bearing groups forming acid groups by acidolysis and repeating units shown as I (R1-3 = alkyl, haloalkyl, halo, alkoxy, trialkylsilyl, trialkylsilyloxy; M = single bond, divalent linkage; R', R'' = H, trialkylmethylsilyl, trialkylmethylsilylmethyl, Cl2Si, trialkoxysilyl, dialkoxymethylsilyl, COA; A = OH, OB, NHB; B = alkyl; R' and R'' may be

linked together via alkylene, CO2CO, CONR'''CO and thereby form ring; R' and R'' may be united, form alkylene, CO2CO, CONR'''CO and thereby form ring; R''' = H, OH, alkyl, OSO2R''''; R'''' = alkyl, trihalomethyl). The acid group-forming repeating units may be CH2CY(LCO2Q) (Y = H, Me, CN, C1; L = single bond, divalent linkage; Q = H, group forming CO2H by acidolysis) or CH[C(0)X2L2A2]CH[C(0)X1L1A1] (X1, X2 = 0, S, NH, NHSO2; L1, L2 = single bond, divalent linkage; A1 = Q, CO2Q; when X1 = O and L1 = single bond, A1 = Q; A2 = H, CN, OH, CO2H, CO2R', COCNHR'', alkyl, cyclic hydrocarbyl, alkoxy, CO2Q; R', R'' = alkyl; Q = H, group forming CO2H by acidolysis). The polymers may contain repeating units derived from maleic anhydride or (N-substituted) maleimides. Preferably, the compns. comprise (A) the above-mentioned polymers, (B) actinic light- or radiation-sensitive acid generators, (C) org. solvents, and optionally (D) org. basses, and (E) surfactants. compns. have high sensitivity yet high resoln., give rectangular patterns with reduced edge roughness of line patterns, and suppressed pattern shifts on pattern transfer to the lower resist layers in O plasma etching process and are suitable for upper layers for bilayered Their pattern formation using ArF excimer laser was exemplified.

L17 ANSWER 24 OF 48 CAPLUS COPYRIGHT 2003 ACS **DUPLICATE 22**

ACCESSION NUMBER:

2001:541843 CAPLUS

DOCUMENT NUMBER: TITLE:

135:129573

Deep UV positive photoresist compositions

containing norbornene- or dicyclopentadiene-based

polymers

INVENTOR (S):

Mizutani, Kazuyoshi

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan

Jpn. Kokai Tokkyo Koho, 30 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

SOURCE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001201855	A2	20010727	JP 2000-8239	20000117
PRIORITY APPLN. INFO.	:		JP 2000-8239	20000117
GI				

$$\begin{array}{c|c} R_{C1} & R_{C4} \\ \hline R_{C2} & R_{C3} \end{array}$$

I

AB The photoresist compns. contain (A) active light- or radiation-sensitive acid generators and (B) resins whose solubilities into alk. solns. are increased by acidolysis and which involve repeating units norbornene derivs. I and/or dicyclopentadiene derivs. II [Rc1-Rc8 = H, (substituted) alkyl, (substituted) cyclohydrocarbyl, halo, cyano, CO2H, C(O)YARc9, C(0)YACO2(CH2)2SiR1R2R3, CO2Rc11, CO2(CH2)2SiR1R2R3; .gtoreq.1 of Rc1-Rc4 = C(O)YACO2(CH2)2SiR1R2R3 or CO2(CH2)2SiR1R2R3; .gtoreq.1 of Rc5-Rc8 = C(0) YACO2(CH2)2SiR1R2R3 or CO2(CH2)2SiR1R2R3; R1-R3 = alkyl, trialkylsilyl, trialkylsilyloxy; Y = O, S, NH, NHSO2, NHSO2NH; Rc9 = CO2H, CO2Rc10 (Rc10 = same as Rc11 or lactones III or IV), CN, OH, (substituted) alkoxyl, CONHRc11, CONHSO2Rc11, or lactones III or IV; Rc11 = (substituted) alkyl, (substituted) cycloalkyl; A = single bond; alkylene, substituted alkylene, O, S, CO, CO2, amide, sulfonamide, urethane, urea; R29-R36 = H, alkyl; a, b = 1, 2]. The compns. may further contain (C) org. bases, (D) silicone-based, F-contg., or nonionic surfactants and (E) org. solvents. In the bilayer resist process, pattern shift on pattern transfer to underlayers while O plasma etching is minimized. Its pattern formation on i-ray resist coated on a Si wafer by exposing to ArF excimer laser was exemplified.

L17 ANSWER 25 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 23

ACCESSION NUMBER: 2001:496392 CAPLUS

DOCUMENT NUMBER:

135:99845

TITLE:

SOURCE:

Positive-working photoresist composition

containing alkali-soluble polymer with silyl group Mizutani, Kazuyoshi; Yanami, Shoichiro

INVENTOR(S):

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 52 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE ----------A2 20010710 JP 2000-303876 20001003 JP 2001188349 JP 1999-298606 A 19991020 PRIORITY APPLN. INFO.:

The compn. comprises (A) a binder resin having a repeating unit bearing a structure (CH2)nSiR1R2R3 (R1-3 = alkyl, haloalkyl, halo, alkoxy, trialkylsilyl, trialkylsilyloxy; n = 0, 1) and a repeating unit bering a group which decomps. by the action of an acid and increases the soly. in an alk. developer at the side chain, (B) a compd. generating an acid by the action of an actinic ray or radiation, (C) a solvent dissolving A and B, (D) an org. base compd., (E) .gtoreq.1 surfactant selected from a fluorosurfactant, a silicone surfactant, and a nonionic surfactant. The compn. shows high resoln. and gives patterns with rectangular cross section and is useful for manuf. of semiconductor device.

L17 ANSWER 26 OF 48 CAPLUS COPYRIGHT 2003 ACS **DUPLICATE 24**

ACCESSION NUMBER: 2001:421234 CAPLUS

DOCUMENT NUMBER: 135:53496

Positive photoresist compositions for TITLE: manufacture of semiconductor devices

Sato, Kenichiro; Kodama, Kunihiko; Mizutani, Kazuyoshi INVENTOR(S):

Fuji Photo Film Co., Ltd., Japan PATENT ASSIGNEE(S): Jpn. Kokai Tokkyo Koho, 59 pp. SOURCE:

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2001159822 A2 20010612 JP 1999-343713 19991202

PRIORITY APPLN. INFO.: JP 1999-343713 · 19991202

OTHER SOURCE(S): MARPAT 135:53496

AB The compns. contain (A) .gtoreq.1 compds., generating sulfonic acids by irradn. of actinic light beam or radiation, selected from Markush structures in the document, (B) acid-decomposable polymers, whose soly. in alkali developers is increased by acids, having specified Si-contg. structural repeating units and specified C:O-contg. structural repeating units, (C) .gtoreq.1 solvents for A and B, (D) org. basic compds., and (E) .gtoreq.1 surfactants selected from F compds., Si compds., and nonionic compds. The compns. show small change in isolated line width for exposure

L17 ANSWER 27 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 25

ACCESSION NUMBER: 2001:423557 CAPLUS

DOCUMENT NUMBER: 135:38893

TITLE: Positive **photoresist** compositions for manufacture of semiconductor devices

INVENTOR(S): Sato, Kenichiro; Kodama, Kunihiko; Mizutani, Kazuyoshi

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 66 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 4

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE --------------A2 B1 JP 1999-343714 JP 2001159812 20010612 19991202 US 6506535 US 2000-698221 20030114 20001030 PRIORITY APPLN. INFO.: JP 1999-307317 A 19991028 JP 1999-331785 A 19991122 JP 1999-338487 A 19991129 JP 1999-343714 A 19991202

OTHER SOURCE(S): MARPAT 135:38893

AB The compns. contain (A) .gtoreq.1 compds., generating sulfonic acids by irradn. of actinic light beam or radiation, selected from Markush structures in the document, (B) polymers, whose soly. in alkali developers is increased by acids, having specified Si-contg. structural repeating units and specified C:O-contg. structural repeating units, (C) .gtoreq.1 solvents for A and B, (D) org. basic compds., and (E) .gtoreq.1 surfactants selected from F compds., Si compds., and nonionic compds. The compns. show small change in isolated line width for exposure amt.

L17 ANSWER 28 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 26

ACCESSION NUMBER: 2001:388948 CAPLUS

DOCUMENT NUMBER: 135:12122

TITLE: Positive-working **photoresist** composition

containing sulfonium compound acid

generator

INVENTOR(S): Sato, Kenichiro; Mizutani, Kazuyoshi PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 65 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 4

PATENT INFORMATION:

PATENT NO.	KIND	DATE		APPLICATION 1	NO.	DATE
JP 2001147536	A2	20010529		JP 1999-3317	85	19991122
US 6506535	B1	20030114		US 2000-6982	21	20001030
PRIORITY APPLN. INFO.	:		JP	1999-307317	Α	19991028
			JP	1999-331785	Α	19991122
			JP	1999-338487	Α	19991129
			JP	1999-343714	Α	19991202

OTHER SOURCE(S):

MARPAT 135:12122

GT

$$\begin{bmatrix} HC = CH \\ n \end{bmatrix} = \begin{bmatrix} CO - O + CH_2 \\ Si - R^2 \\ R^3 \end{bmatrix}_{n}$$

AB The compn. comprises (A) a sulfonium compd. R1R2R3S+.Z- [R1-3 = (substituted) alkyl, (substituted) aryl; Z- = counter anion] which generates an acid by the action of the actinic ray or radiation, (B) an acid-decomposable resin having repeating units I (M1 = atoms forming alicyclic structure; n = 1, 2; L = bond, linkage with (n + 1) valences; R', R'', R''' = alkyl, Ph, trialkylsilyl,trialkylsilyloxy) and .gtoreq.1 of II and III (Z = 0, NR3; R3 = H, alkyl, OSO2R4; R4 = alkyl, trihalomethyl; X1-2 = H, S, NH, NHSO2; A1-2 = bond, divalent linkage; R1-2 = H, CN, OH, CO2H, CO2R5, CONHR6, alkyl, alkoxy, cyclic hydrocarbon which may have ester or carbonyl group in ring-forming bond; R6 = alkyl), (C) .gtoreq.1 solvent dissolving (A) and (B), (D) an org. base compd., and (E) .gtoreq.1 surfactant selected from F-, Si-, and nonionic surfactant. Particle generation in the resist soln. is prevented, the compn. shows high sensitivity and resoln. and is useful for manuf. of contact hole patterns in semiconductor device fabrication.

L17 ANSWER 29 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 27

ACCESSION NUMBER: 2001:299131 CAPLUS

DOCUMENT NUMBER: 134:334282

TITLE: Far-UV-sensitive positive photoresist

compositions containing lactone-ring-bearing polymers

INVENTOR(S): Sato, Kenichiro; Adegawa, Yutaka; Aogo, Toshiaki

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 53 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2001117234 20010427 JP 1999-298782 19991020 PRIORITY APPLN. INFO.: JP 1999-298782 19991020

AΒ The compns., showing good developability and excellent storage stability, comprise photoacid generators, polymers comprising (i) [CH(COX1A1R1)CH(COX2A2R2)] [R1, R2 = H, cyano, OH, CO2H, CO2R5] [R5 =alkyl, cyclic hydrocarbyl, Y1, Y2 (R21-30 = H, alkyl; a, b = 1, 2)], CONHR6 (R6 = alkyl, cyclic hydrocarbyl), CONHSO2R6, alkyl(oxy), cyclic hydrocarbyl, Y1, Y2; X = O, S, NH, NHSO2, NHSO2NH; A = single bond, bivalent linkage] and/or I [Z2 = O, NR3 [R3 = H, OH, OSO2R4 [R4 = (halo)alkyl, cycloalkyl, camphor residue]]] and (ii) II [R11, R12 = H, cyano, halo, alkyl; Z = alicyclic groups], and optional N-contg. basic compds. The polymers have .gtoreq.2 resins bearing acid-decomposable groups (AG) with different AG mol. concn. from each other.

L17 ANSWER 30 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 28

ACCESSION NUMBER: 2001:299130 CAPLUS

DOCUMENT NUMBER: 134:318692

TITLE: Positive photoresist compositions providing

line patterns with excellent edge sharpness

INVENTOR(S): Mizutani, Kazuyoshi

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan SOURCE:

Jpn. Kokai Tokkyo Koho, 35 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent Japanese LANGUAGE:

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE ----------____ JP 2001117233 A2 20010427 JP 1999-298605 19991020 PRIORITY APPLN. INFO.: JP 1999-298605 19991020 The compns. comprise (A) acid-decomposable polymers comprising (i) [CH2C[(CH2)nSiR1R2R3]H] [R1-3 = (halo)alkyl, halo, alkoxy,trialkylsilyl(oxy); n = 0, 1] and (ii) [CH2CY(LCO2Q)] [Y = H, Me, cyano, Cl; L = single bond, bivalent linkage; Q = H, acid-decomposable groups] and/or [CH(COX2L2A2)CH(COX1L1A1)] [X1, X2 = 0, S, NH, NHSO2; L1, L2 = single bond, bivalent linkage; A1 = Q, CO2Q; A2 = H, cyano, OH, CO2H, CO2R', CONHR", alkyl(oxy), cyclic hydrocarbyl, CO2Q (R', R" = alkyl)], (B) photoacid generators, (C) org. solvents, (D) basic org. compds., (E) F- and/or Si-bearing surfactants and/or nonionic surfactants. The photoacid generators may generate org. sulfonic acids upon irradn.

L17 ANSWER 31 OF 48 CAPLUS COPYRIGHT 2003 ACS **DUPLICATE 29**

2001:143826 CAPLUS ACCESSION NUMBER:

134:200525 DOCUMENT NUMBER:

TITLE: Positive-working photoresist composition for

far ultraviolet ray exposure

Aogo, Toshiaki; Sato, Kenichiro; Kodama, Kunihiko INVENTOR(S):

Fuji Photo Film Co., Ltd., Japan PATENT ASSIGNEE(S): Jpn. Kokai Tokkyo Koho, 55 pp. SOURCE:

CODEN: JKXXAF

DOCUMENT TYPE:

Patent Japanese

LANGUAGE:

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

KIND DATE PATENT NO. ____ APPLICATION NO. DATE

-----JP 1999-234240 19990820

JP 2001056557 A2 20010227 PRIORITY APPLN. INFO.:

JP 1999-234240

$$\begin{bmatrix} R^2 \\ R^3 \end{bmatrix}_{\mathfrak{m}} \begin{bmatrix} R^4 \\ R^5 \end{bmatrix}_{\mathfrak{n}}$$

The compn. comprises (A) a compd. generating acid by actinic ray or AB radiation, (B) a resin contg. I [R1 = H, C1-4 alkyl; R2-7 = H, (substituted) alkyl, cycloalkyl, alkenyl, .gtoreq.1 of R6 and R7 is not H, R6 and R7 may form a ring; m, n = 0, 1] as a repeating unit and whose sol. in alkali is increased by the action of acid, and (C) a fluoro- and/or silicone-type surfactant. The photoresist shows high sensitivity to far UV ray and generation of development defect and edge roughness is prevented.

L17 ANSWER 32 OF 48 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 30

ACCESSION NUMBER:

2001:803974 CAPLUS

DOCUMENT NUMBER:

136:110038

TITLE:

Evaluation of the standard addition method to determine rate constants for acid generation in

chemically amplified photoresist at 157 nm

AUTHOR (S):

Pawloski, Adam Richard; Szmanda, Charles R.; Nealey,

Paul F.

CORPORATE SOURCE:

Department of Chemical Engineering, University of

Wisconsin, Madison, USA

SOURCE:

Proceedings of SPIE-The International Society for Optical Engineering (2001), 4345 (Pt. 2, Advances in Resist Technology and Processing XVIII), 1056-1065

CODEN: PSISDG; ISSN: 0277-786X

PUBLISHER:

SPIE-The International Society for Optical Engineering

DOCUMENT TYPE:

Journal

LANGUAGE:

English

The rate consts. for acid generation (C parameter) in chem. amplified photoresist are detd. for four photoacid generators (norbornene dicarboximidyl triflate, tri-Ph sulfonium triflate, bis-4-tert-butylphenyliodonium perfluorooctanesulfonate, and bis-4-tert-butylphenyliodonium triflate) under exposure to 157 nm radiation using a std. addn. technique. The technique utilizes an in film neutralization of photogenerated acid by base quencher to det. the increase in exposure energy necessary to produce an equiv. fee acid concn. at each loading of base. The authors present a general model to interpret the data that also accounts for the strong absorption of radiation by the resist film. An av. absorption coeff. of 13.2 .mu.m -1 (base e) has been measured at 157 nm for these resist films. Results from 157 nm irradn. are compared to deep-UV and ionizing radiation, indicating that resist photochem. at 157 nm includes processes important to both energy regimes.

REFERENCE COUNT: 32 THERE ARE 32 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L17 ANSWER 33 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 31

ACCESSION NUMBER: 2000:115243 CAPLUS

DOCUMENT NUMBER: 132:158926

TITLE: Positive-working photosensitive resin

composition useful in production of semiconductor

devices

INVENTOR(S): Kawabe, Yasumasa; Sato, Kenichiro; Aogo, Toshiaki

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 13 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE ----- ---- ---- -----______ JP 2000047385 A2 20000218 JP 1998-170197 19980617 JP 1998-144436 19980526 PRIORITY APPLN. INFO.: The title resin compn. contains (a) a polymer which has a cyclic aliph. hydrocarbon skeleton and is cleaved in the action of acid to become alkali sol., (b) a compd. generating an acid upon activating radiation irradn., (c) a carboxylic acid anhydride with mol. wt. .ltoreq.1000, (d) a N-contg. basic compd., and (e) F- and/or Si-type surfactant. The compn. shows improved developability and provides high resoln. patterns with good profile and high residual film rate by using deep UV rays, esp. ArF excimer laser beams.

L17 ANSWER 34 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 32

ACCESSION NUMBER: 2000:67678 CAPLUS

DOCUMENT NUMBER: 132:130026

TITLE: Positive-working resist composition suited

for use in deep UV ray exposure

INVENTOR(S): Aogo, Toshiaki

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 44 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

KIND DATE APPLICATION NO. DATE PATENT NO. ----------JP 2000029219 A2 20000128 JP 1998-197730 19980713 JP 1998-197730 19980713 PRIORITY APPLN. INFO.: The title resist compn. contains (a) a compd. generating an acid upon activating ray or radiation irradn., (b) a resin having polycyclic alicyclic groups and CO2H groups, (c) a compd. having .gtoreq.2 groups CR1R2C:CR3Z [R1-3 = H, (substituted) alkyl, (substituted) cycloalkyl, 2 of R13 may link each other to form a ring structure comprising 3-8 C atoms and heteroatoms; Z = O, S, SO2, NH], (d) a cyclic aliph. org. carboxylic acid with mol. wt. .ltoreq.1000 and/or a naphthalene ring-contg. org. carboxylic acid, (e) a N-contg. basic compd., and (f) a F-type and/or Si-type surfactant. The compn. shows improved developability and provides a resoln. pattern with high residual film rate and good profile using deep UV rays, esp., ArF excimer lasers.

L17 ANSWER 35 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 33

ACCESSION NUMBER: 2000:67677 CAPLUS

DOCUMENT NUMBER: 132:130025

TITLE: Positive-working resist composition suited

for use in deep ultraviolet ray exposure

Aogo, Toshiaki INVENTOR(S):

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 44 pp. SOURCE:

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE --------------JP 2000029218 A2 20000128 JP 1998-197729 19980713 PRIORITY APPLN. INFO.: JP 1998-197729 The title resist compn. contains (a) a compd. generating an acid

upon activating ray or radiation irradn., (b) a resin having polycyclic alicyclic groups and CO2H groups, (c) a compd. having .gtoreq.2 groups CR1R2C:CR3Z [R1-3 = H, (substituted) alkyl, (substituted) cycloalkyl, 2 of R13 may link each other to form a ring structure comprising 3-8 C atoms and heteroatoms; Z = O, S, SO2, NH], (d) a N-contg. basic compd., and (e) a F-type and/or Si-type surfactant. The compn. shows improved developability and provides a pattern with high residual film rate and good profile using deep UV rays, esp., ArF excimer lasers.

L17 ANSWER 36 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 34

ACCESSION NUMBER: 2000:441519 CAPLUS

DOCUMENT NUMBER:

133:81571

TITLE:

Photoresist composition suitable for deep-UV

wavelength imaging

INVENTOR(S):

Trefonas, Peter, III; Taylor, Gary N.

PATENT ASSIGNEE(S): SOURCE:

Shipley Company LLC, USA Eur. Pat. Appl., 14 pp.

CODEN: EPXXDW

DOCUMENT TYPE:

Patent.

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

DATE 6 PATENT NO. KIND APPLICATION NO. DATE _____ _____ ---------

EP 1014193 EP 1999-125625 **A1** 20000628 19991222 R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT,

IE, SI, LT, LV, FI, RO

JP 2000298348 A2 20001024 JP 1999-376940 19991224 US 1998-219468 A 19981223 PRIORITY APPLN. INFO.:

The present invention provides a novel photoresist compn. suitable for deep-UV wavelength imaging comprising a resin

binder, a photosensitive acid generator, and

an amine additive. In a first aspect, the amine additive preferably is nonarom., has from about 9 to about 16 carbon atoms, contains no primary or secondary amine groups, and/or contains no multiple tertiary amine groups where two tertiary groups are sepd. by a linkage of optionally substituted ethylene. In a related aspect, the amine is a nonarom. amine comprising either a tertiary nitrogen alicyclic ring member which is at a junction position of at least two rings of a multiring compd. or a tertiary nitrogen that is not a ring member and substituted by at least two tertiary or quaternary carbon radicals.

REFERENCE COUNT: THERE ARE 6 CITED REFERENCES AVAILABLE FOR THIS 6 RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L17 ANSWER 37 OF 48 USPATFULL

2000:142069 USPATFULL ACCESSION NUMBER:

TITLE: Resist composition and patterning process

Satoshi, Watanabe, Nakakubiki-gun, Japan INVENTOR(S):

> Osamu, Watanabe, Nakakubiki-gun, Japan Tomoyoshi, Furihata, Usui-gun, Japan Yoshifumi, Takeda, Nakakubiki-gun, Japan Shigehiro, Nagura, Nakakubiki-gun, Japan Toshinobu, Ishihara, Nakakubiki-gun, Japan

Tsuquo, Yamaoka, Funabashi, Japan

PATENT ASSIGNEE(S): Shin-Etsu Chemical Co., Ltd., Tokyo, Japan (non-U.S.

corporation)

NUMBER KIND DATE -----

PATENT INFORMATION: US 6136502 20001024

APPLICATION INFO.: US 1998-167567 19981007 (9)

> DATE NUMBER _____

PRIORITY INFORMATION: JP 1997-291681 19971008

DOCUMENT TYPE: Utility FILE SEGMENT: Granted PRIMARY EXAMINER: Chu, John S.

LEGAL REPRESENTATIVE: Millen, White, Zelano & Branigan, P.C.

NUMBER OF CLAIMS: 19 EXEMPLARY CLAIM: 1 LINE COUNT: 2356

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

A resist composition comprising (A) an organic solvent; (B) at least two polymers with weight average molecular weights of

1,000-500,000, which have at least one type of acid labile group and are crosslinked within a molecule and/or between molecules with crosslinking

groups having C--O--C linkages; and (C) a photoacid

generator is sensitive to high-energy radiation, has excellent

sensitivity, resolution, and plasma etching resistance, and provides resist patterns of outstanding thermal stability and reproducibility. Patterns obtained with this resist

composition are less prone to overhanging and have excellent dimensional

controllability. The resist composition is suitable as a

micropatterning material for VLSI fabrication because it has a low absorption at the exposure wavelength of a KrF excimer laser, thus

enabling the easy formation of a finely defined pattern having sidewalls perpendicular to the substrate.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L17 ANSWER 38 OF 48 USPATFULL

2000:142068 USPATFULL ACCESSION NUMBER:

Polymers and photoresist compositions TITLE:

comprising same

Trefonas, III, Peter, Medway, MA, United States INVENTOR(S):

Taylor, Gary N., Northboro, MA, United States Barclay, George G., Jefferson, MA, United States

Shipley Company, L.L.C., Marlborough, MA, United States PATENT ASSIGNEE(S):

(U.S. corporation)

NUMBER KIND DATE -----

US 6136501 20001024 PATENT INFORMATION: 19980828 (9)

US 1998-143462 APPLICATION INFO.: DOCUMENT TYPE: Utility

FILE SEGMENT: Granted Chu, John S. PRIMARY EXAMINER: Clarke, Yvette M ASSISTANT EXAMINER:

Corless, Peter F., Frickey, Darryl P., Cairns, S. LEGAL REPRESENTATIVE:

Matthew

NUMBER OF CLAIMS: 30 EXEMPLARY CLAIM: 1,20 LINE COUNT: 865

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

The present invention provides novel polymers and photoresist compositions that comprise the polymers as a resin binder component. The photoresist compositions of the invention can provide highly resolved relief images upon exposure to short wavelengths, including 193 nm and 248 nm. The resists of the invention are also useful or imaging at other wavelengths such as 365 nm. Polymers of the invention include those that comprise a photogenerated acid-labile unit that is ester group that comprises an alkyl moiety having about 5 or more carbon atoms and at least two secondary, tertiary or quaternary carbon atoms. The alkyl moiety of the ester group can be a noncyclic or single ring alicyclic group. The carboxyl (C.dbd.O(O)) oxygen of the ester group is often preferably

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L17 ANSWER 39 OF 48 USPATFULL

ACCESSION NUMBER: 2000:57508 USPATFULL

TITLE: Positive-working photosensitive composition

INVENTOR(S): Kodama, Kunihiko, Shizuoka, Japan

directly bonded to a quaternary carbon atom.

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Kanagawa, Korea, Republic of

(non-U.S. corporation)

NUMBER DATE

PRIORITY INFORMATION: JP 1998-66990 19980317

DOCUMENT TYPE: Utility
FILE SEGMENT: Granted
PRIMARY EXAMINER: Baxter, Jar

PRIMARY EXAMINER: Baxter, Janet ASSISTANT EXAMINER: Lee, Sin J.

LEGAL REPRESENTATIVE: Sughrue, Mion, Zinn, Macpeak & Seas, PLLC

NUMBER OF CLAIMS: 7
EXEMPLARY CLAIM: 1
LINE COUNT: 1480

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

The present invention provides a positive-working photosensitive composition which comprises (a) a basic nitrogen-containing compound having a polycyclic structure represented by formula (I) and (b) at least one of compounds represented by formulae (II) to (IV) defined in the specification: wherein Y and Z may be the same or different and each represent a straight-chain, branched or cyclic alkylene group, which may contain a hetero atom or may be substituted. The positive-working photosensitive composition which exhibits no reduction of width of resist pattern or no T-top deformation of surface shape of resist pattern with time between after exposure and heat treatment without causing sensitivity drop.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L17 ANSWER 40 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 35

ACCESSION NUMBER: 1999:752381 CAPLUS

DOCUMENT NUMBER: 132:17147

TITLE: Positive-working photosensitive composition

INVENTOR(S): Kodama, Kunihiko

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 43 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

KIND DATE PATENT NO. APPLICATION NO. DATE -----______ JP 1999-70372 JP 11327149 A2 19991126 US 6060213 A 20000509 19990316 US 1999-270516 19990317 PRIORITY APPLN. INFO.: JP 1998-66990 19980317

OTHER SOURCE(S): MARPAT 132:17147

For diagram(s), see printed CA Issue.

AB The title photosensitive compn. contains (a) a polycyclic basic N-contg. compd. I (Y, Z = straight-chain, branched or cyclic alkylene which may contain heteroatoms and may be substituted), (b) .gtoreq.1 compd. selected from II-IV [R1-37 = H, straight-chain, branched or cyclic alkyl, straight-chain, branched or cyclic alkoxy, OH, halo, SR38 (R38 = straight-chain, branched or cyclic alkyl, aryl); X- = benzenesulfonic acid, naphthalenesulfonic acid or anthracene sulfonic acid anion which has (i) .qtoreq.1 group selected from branched or cyclic C.qtoreq.8 alkyl and alkoxy, .gtoreq.2 groups selected from straight-chain, branched or cyclic C4-7 alkyl and alkoxy, or .gtoreq.3 groups selected from straight-chain, branched or cyclic C1-3 alkyl and alkoxy or (ii) .gtoreq.1 group selected from ester, R39CO, R40CONH, R41NH, R42OCONH, R43NHCO2, R44NHCONH, R45NHCSN, R46SO2NH, and NO2 groups (R39-46 = straight-chain, branched or cyclic alkyl, aryl)], which generates an acid upon activating radiation irradn., and (c) a resin having groups which are decompd. by the action of acid to increase the soly. in alkali developing solns. compn. may contain (a), (b), (d) a low-mol.-wt. dissoln.-inhibiting compd. with mol. wt. .ltoreq.3000 which has an acid-decomposable group and of which the soly. in alkali developing solns. increases by the action of acid, and (e) a resin insol. in water and sol. in alkali developing solns. The compn. shows high photosensitivity and provides a high resoln. pattern with good profile independent of the elapse of time from exposure to bake.

L17 ANSWER 41 OF 48 CAPLUS COPYRIGHT 2003 ACS DUPLICATE 36

ACCESSION NUMBER:

1999:752377 CAPLUS

DOCUMENT NUMBER:

132:7565

TITLE:

Positive-working photosensitive resin

composition useful in production of semiconductor

devices

INVENTOR(S):

Kawabe, Yasumasa; Sato, Kenichiro; Aogo, Toshiaki

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 14 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

KIND DATE PATENT NO. APPLICATION NO. DATE _____ ------JP 11327145 A2 19991126 JP 1998-132291 19980514 19980514 JP 1998-132291 PRIORITY APPLN. INFO.: The title resin compn. contains (a) a cyclic aliph. hydrocarbon skeleton structure-contg. polymer that is decompd. by the action of acid to become alkali-sol., (b) a compd. that generates an acid upon active ray or radiation irradn., (c) a sulfonamide structure-contg. compd. with mol. wt. .ltoreq.1000, (d) a N-contg. basic compd., and (e) a F-type and/or Si-type surfactant. The compn. shows improved developability and provides a high resoln. pattern with good profile by using deep UV rays, esp., ArF

excimer laser beams and is useful for manuf. of semiconductor devices.

L17 ANSWER 42 OF 48 CAPLUS COPYRIGHT 2003 ACS

DUPLICATE 37

ACCESSION NUMBER:

1999:819124 CAPLUS

DOCUMENT NUMBER:

132:71367

TITLE:

Positive photoimaging composition for photofabrication

INVENTOR(S):

Kawabe, Yasumasa; Sato, Kenichiro; Aoai, Toshiaki

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan

SOURCE:

Eur. Pat. Appl., 57 pp. CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

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E	9675	22		A:	1	1999	1229]	EΡ	199	9-1	1196	53	1999	0625		
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		ΙE,	SI,	LT,	LV,	FI,	RO											
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JI	2000	0197	35	A:	2	2000	0121		į.	JP	199	8-1	8627	72	1998	0701		
J	2000	0197	36	A:	2	2000	0121			JP	199	8-1	8627	73	1998	0701		
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GΙ

$$\begin{array}{c}
x - co_2 R^5 \\
c = o \\
0 \\
R^1 R^2 \\
CH \\
R^3 R^4
\end{array}$$

A UV-sensitive pos. photoimaging compn. for photofabrication comprises a AB photoacid generator, a nitrogen-contg. basic compd., a polymer having the group represented by the formula I (R1-4 = H, OH, carboxyl, alkyl, alkoxy, or cycloalkyl, provided that either R1 and R3 or R2 and R4 may be bonded to each other to form a ring; X = a bivalent org. group having 2-20 carbon atoms; R5 = H, carboxyl, alkyl, cycloalkyl, or such a group that the -CO2R5 functions as a group which decomps. by the action of an acid; Z = a group of atoms which form a cyclohexane or decalin ring in combination with carbon atoms), and at least of a fluorine-contg. surfactant and a silicone surfactant.

REFERENCE COUNT:

THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

Ι

ACCESSION NUMBER:

1999:246939 CAPLUS

DOCUMENT NUMBER:

130:274098

TITLE: '

Photoresist composition

INVENTOR(S):

Watanabe, Satoshi; Watanabe, Osamu; Furihata, Tomoyoshi; Takeda, Yoshifumi; Nagura, Shigehiro;

Ishihara, Toshinobu; Yamaoka, Tsuguo Shin-Etsu Chemical Co., Ltd., Japan

PATENT ASSIGNEE(S):

SOURCE:

Eur. Pat. Appl., 82 pp. CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
	-			
EP 908783	A1	19990414	EP 1998-308175	19981008

EP 908783 В1 20020731

R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO

JP 1998-299177 19981006 JP 11190904 A2 19990713 US 6136502 US 1998-167567 19981007 Α 20001024 PRIORITY APPLN. INFO.: JP 1997-291681 A 19971008

A photoresist compn. comprises (A) an org. solvent, (B) at least two polymers with wt.-av. mol. wts. of 1000-500,000, which have at least one type of acid labile groups and are crosslinked within a mol. and/or between mols. with crosslinking groups having C-O-C linkages, and (C) a photoacid generator. The photoresist compn.

has excellent sensitivity and resoln. and provides resist patterns of outstanding thermal stability, reproducibility, and plasma etching resistance. Patterns obtained with the photoresist compn. are less prone to overhanging and have excellent dimensional controllability. The photoresist compn. is suitable as a micropatterning material for VLSI fabrication.

REFERENCE COUNT:

THERE ARE 7 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

DUPLICATE 39

L17 ANSWER 44 OF 48 CAPLUS COPYRIGHT 2003 ACS

7

2000:128097 CAPLUS

ACCESSION NUMBER: DOCUMENT NUMBER:

132:271599

TITLE:

Measuring acid generation efficiency in chemically

amplified resists with all three beams

AUTHOR (S):

Szmanda, Charles R.; Brainard, Robert L.; Mackevich, Joseph F.; Awaji, Akira; Tanaka, Tsutomu; Yamada, Yutaka; Bohland, John; Tedesco, Serge; Dal'Zotto, Bernard; Bruenger, Wilhelm; Torkler, Michael; Fallmann, Wolfgang; Loeschner, Hans; Kaesmaier, Rainer; Nealey, Paul M.; Pawloski, Adam R.

CORPORATE SOURCE:

Shipley Company, Marlborough, MA, 01752, USA

Journal of Vacuum Science & Technology, B: SOURCE:

Microelectronics and Nanometer Structures (1999),

17(6), 3356-3361

CODEN: JVTBD9; ISSN: 0734-211X American Institute of Physics

PUBLISHER:

Journal

DOCUMENT TYPE: LANGUAGE:

English

A method for measuring acid generation efficiency is developed to det. the relative efficiency of lithog. resists acid generators (PAGs) upon radiation with photon-, electron-, and ion-beams. In this method, chem. amplified resists are prepd. with varying amts. of base quencher (1.8-diazabicyclo[5.4.0]undec-7-ene), coated into thin films (1000 .ANG.), and exposed. Linear plots of the base concn. against the threshold exposure dose for each resist yield the threshold acid concn. and the acid generation rate const. for

each PAG. The acid-generating efficiency of the four PAGs: norbornenedicarboximidyl triflate, triphenylsulfonium triflate, bis-4-tert-butylphenyliodonium perfluorooctanesulfonate, and bis-4-tert-butylphenyliodonium triflate upon irradn. with deep-UV (248 nm), extreme-UV (13.4 nm), x-ray (1 nm), electron-beam (30 and 50 keV), and He+ ions were evaluated.

REFERENCE COUNT:

THERE ARE 36 CITED REFERENCES AVAILABLE FOR THIS 36 RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L17 ANSWER 45 OF 48 USPATFULL

ACCESSION NUMBER:

97:83772 USPATFULL

TITLE:

Process for thermochemical generation of acid and for thermal imaging, and imaging medium for use therein

INVENTOR(S):

Boggs, Roger A., Wayland, MA, United States Grasshoff, Jurgen M., Hudson, MA, United States Mischke, Mark R., Arlington, MA, United States Puttick, Anthony J., Arlington, MA, United States Telfer, Stephen J., Arlington, MA, United States Waller, David P., Lexington, MA, United States Waterman, Kenneth C., Arlington, MA, United States

PATENT ASSIGNEE(S):

Polaroid Corporation, Cambridge, MA, United States

(U.S. corporation)

NUMBER KIND DATE ______

PATENT INFORMATION:

US 5667943 19970916 US 1996-630967 19960408 (8)

APPLICATION INFO.: RELATED APPLN. INFO.:

Division of Ser. No. US 1994-345073, filed on 28 Nov 1994, now patented, Pat. No. US 5534393 which is a division of Ser. No. US 1993-106353, filed on 13 Aug 1993, now patented, Pat. No. US 5401619 which is a division of Ser. No. US 1992-965172, filed on 23 Oct

1992, now patented, Pat. No. US 5278031

DOCUMENT TYPE:

Utility

FILE SEGMENT:

Granted

PRIMARY EXAMINER:

Letscher, Geraldine

LEGAL REPRESENTATIVE:

Cole, David J.

NUMBER OF CLAIMS:

EXEMPLARY CLAIM:

NUMBER OF DRAWINGS:

3 Drawing Figure(s); 3 Drawing Page(s)

LINE COUNT:

1498

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

Certain squaric acid derivatives are useful for the thermochemical AB generation of acid. The squaric acid derivatives may be used in imaging media in conjunction with acid-sensitive materials which undergo a color change when contacted by the acid generated from the squaric acid derivatives. Preferably, the acid-sensitive materials undergo an irreversible color change, so that the image can be fixed by neutralizing all the acid generated with excess base, thereby preventing

further color change in the image during long term storage.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L17 ANSWER 46 OF 48 USPATFULL

ACCESSION NUMBER:

96:60579 USPATFULL

TITLE:

Process for thermochemical generation of acid and for

thermal imaging

INVENTOR (S):

Boggs, Roger A., Wayland, MA, United States Grasshoff, Jurgen M., Hudson, MA, United States Mischke, Mark R., Arlington, MA, United States Puttick, Anthony J., Arlington, MA, United States Telfer, Stephen J., Arlington, MA, United States Waller, David P., Lexington, MA, United States Waterman, Kenneth C., Arlington, MA, United States PATENT ASSIGNEE(S): Polaroid Corporation, Cambridge, MA, United States

(U.S. corporation)

NUMBER KIND DATE -----US 1994-345073 PATENT INFORMATION: 19960709 APPLICATION INFO.: 19941128 (8)

Division of Ser. No. US 1993-106353, filed on 13 Aug RELATED APPLN. INFO.:

1993, now patented, Pat. No. US 5401619 which is a division of Ser. No. US 1992-965172, filed on 23 Oct

1992, now patented, Pat. No. US 5278031

DOCUMENT TYPE: Utility FILE SEGMENT: Granted

PRIMARY EXAMINER: Letscher, Geraldine

LEGAL REPRESENTATIVE: Cole, David J.

NUMBER OF CLAIMS: 13 EXEMPLARY CLAIM: 1,2

NUMBER OF DRAWINGS: 3 Drawing Figure(s); 3 Drawing Page(s)

LINE COUNT: 1515

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AB Certain squaric acid derivatives are useful for the thermochemical generation of acid. The squaric acid derivatives may be used in imaging media in conjunction with acid-sensitive materials which undergo a color change when contacted by the acid generated from the squaric acid derivatives. Preferably, the acid-sensitive materials undergo an irreversible color change, so that the image can be fixed by

neutralizing all the acid generated with excess base, thereby preventing

further color change in the image during long term storage.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L17 ANSWER 47 OF 48 USPATFULL

ACCESSION NUMBER: 95:27187 USPATFULL

Process for thermochemical generation of acid and for TITLE:

thermal imaging, and imaging medium for use therein

Boggs, Roger A., Wayland, MA, United States INVENTOR(S):

Grasshoff, Jurgen M., Hudson, MA, United States Mischke, Mark R., Arlington, MA, United States Puttick, Anthony J., Arlington, MA, United States Telfer, Stephen J., Arlington, MA, United States Waller, David P., Lexington, MA, United States Waterman, Kenneth C., Arlington, MA, United States Polaroid Corporation, Cambridge, MA, United States

(U.S. corporation)

NUMBER KIND ______

PATENT INFORMATION: US 5401619 19950328 APPLICATION INFO.: US 1993-106353 19930813 (8)

Division of Ser. No. US 1992-965172, filed on 23 Oct RELATED APPLN. INFO.:

1992, now patented, Pat. No. US 5278031

DOCUMENT TYPE: Utility Granted FILE SEGMENT:

Bowers, Jr., Charles L. PRIMARY EXAMINER: Letscher, Geraldine ASSISTANT EXAMINER:

LEGAL REPRESENTATIVE: Cole, David J.

NUMBER OF CLAIMS: 12 EXEMPLARY CLAIM:

PATENT ASSIGNEE(S):

NUMBER OF DRAWINGS: 3 Drawing Figure(s); 3 Drawing Page(s)

LINE COUNT: 1536

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

Certain squaric acid derivatives are useful for the thermochemical generation of acid. The squaric acid derivatives may be used in imaging media in conjunction with acid-sensitive materials which undergo a color change when contacted by the acid generated from the squaric acid derivatives. Preferably, the acid-sensitive materials undergo an irreversible color change, so that the image can be fixed by neutralizing all the acid generated with excess base, thereby preventing further color change in the image during long term storage.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L17 ANSWER 48 OF 48 USPATFULL

ACCESSION NUMBER: 94:3655 USPATFULL

TITLE: Process for thermochemical generation of squaric acid

and for thermal imaging, and imaging medium for use

therein

INVENTOR(S): Boggs, Roger A., Wayland, MA, United States

Grasshoff, Jurgen M., Hudson, MA, United States Mischke, Mark R., Arlington, MA, United States Puttick, Anthony J., Arlington, MA, United States Telfer, Stephen J., Arlington, MA, United States Waller, David P., Lexington, MA, United States Waterman, Kenneth C., Arlington, MA, United States

PATENT ASSIGNEE(S): Polaroid Corporation, Cambridge, MA, United States

(U.S. corporation)

NUMBER KIND DATE

PATENT INFORMATION: US 5278031 19940111

APPLICATION INFO.: US 1992-965172 19921023 (7)

DOCUMENT TYPE: Utility FILE SEGMENT: Granted

PRIMARY EXAMINER: Bowers, Jr., Charles L. ASSISTANT EXAMINER: Letscher, Geraldine

LEGAL REPRESENTATIVE: Cole, David J.

NUMBER OF CLAIMS: 21 EXEMPLARY CLAIM: 1

NUMBER OF DRAWINGS: 3 Drawing Figure(s); 3 Drawing Page(s)

LINE COUNT: 1517

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AB Certain squaric acid derivatives are useful for the thermochemical generation of acid. The squaric acid derivatives may be used in imaging media in conjunction with acid-sensitive materials which undergo a color change when contacted by the acid generated from the squaric acid derivatives. Preferably, the acid-sensitive materials undergo an irreversible color change, so that the image can be fixed by neutralizing all the acid generated with excess base, thereby preventing further color change in the image during long term storage.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L26 ANSWER 53 OF 53 USPATFULL

ACCESSION NUMBER: 74:17590 USPATFULL

TITLE: FLAME RETARDANT, INTUMESCENT AND NON-BURNING FLEXIBLE

POLYURETHANE FOAM

INVENTOR(S): Krentz, Jr., George Robert, Twin Oaks, PA, United

States

PATENT ASSIGNEE(S): Scott Paper Company, Philadelphia, PA, United States

(U.S. corporation)

NUMBER KIND DATE

DAMENTE TATOONAMETON 110 2002062

PATENT INFORMATION: US 3803063 19740409

APPLICATION INFO.: US 1969-866372 19691014 (4)

DOCUMENT TYPE: Utility FILE SEGMENT: Granted

PRIMARY EXAMINER: Czaja, Donald E. ASSISTANT EXAMINER: Rzucidlo, Eugene C.

LEGAL REPRESENTATIVE: DeBenedictis, Nicholas J., Kane, John W.

NUMBER OF CLAIMS: 11 LINE COUNT: 476

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AB A non-burning imparting amount of a mixture of (a) a nitrogen and phosphorus-containing compound, and (b) a polycondensate of polymerized

unsaturated fatty acids with aliphatic amines is incorporated in a

foamable polyurethane-forming reaction mixture to produce a

flame-retardant, intumescent and non-burning flexible polyurethane foam

which would otherwise be consumed by exposure to a flame.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> d 126 and (?acid (w) generator)
'(?ACID,(W)' IS NOT VALID HERE

=> s 126 and (?acid (w) generator)

L27 1 L26 AND (?ACID (W) GENERATOR)

=> d 127 1 ibib abs hitstr

L27 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2003 ACS ACCESSION NUMBER: 2000:143347 CAPLUS

DOCUMENT NUMBER: 132:201042

TITLE: Radiation-sensitive resin composition useful

. as **resist**

INVENTOR(S): Chiba, Takashi; Kobayashi, Eiichi; Iwanaga, Shinichiro

PATENT ASSIGNEE(S): JSR Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 21 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2000066382 A2 20000303 JP 1998-236167 19980821

PRIORITY APPLN. INFO.: JP 1998-236167 19980821

GI

AB The title resin compn. contains (a) a copolymer having repeating units I and CR2(CO2R3)CH2 [R1, R2 = H or Me; R3 = tert-Bu or CR4R5CHR6COR7 (R4, R5 = H, C1-6 straight-chain or branched alkyl, 5- to 8-membered cyclic alkyl, R4 and R5 may link each other to form a 5- to 8-membered carbon ring along with the C atom in the group; R6, R7 = H, C1- 6 straight-chain or branched alkyl, 5- to 8-membered cyclic alkyl, R6 and R7 may link each other to form a 5- to 8-membered carbon ring along with the 2 C atoms in the group)], (b) a radiation-sensitive acid generator, and (c) a OH-contg. basic compd. The compn. shows high sensitivity esp. toward far UV rays, x-ray, and electron beams and provides high resoln. patterns with good profile even on basic substrates.

RL: TEM (Technical or engineered material use); USES (Uses) (radiation resist contg. hydroxystyrene-Bu acrylate copolymer, acid generator, and basic compd.)

RN 17121-34-5 CAPLUS

CN

2-Propanol, 1,1',1'',1'''-[[(2-hydroxypropyl)imino]bis(2,1-ethanediylnitrilo)]tetrakis- (9CI) (CA INDEX NAME)